



LIGITEK

NPN SILICON PHOTOTRANSISTOR LED LAMPS		LPT3233		SERIES		
<p>Package Dimension</p> <p>1.EMITTER 2.COLLECTOR</p> <p>Note:1.All dimension are in millimeter tolerance is $\pm 0.25\text{mm}$ unless otherwise noted 2.Specifications are subject to change without notice</p>				<p>Features</p> <ul style="list-style-type: none"> High illumination sensitivity Stable characteristics Spectrally and mechanically matched with IR emitter <p>Description</p> <p>The LPT3233 series are silicon nitride passivated NPN planar phototransistors with exceptionally stable characteristics and high illumination sensitivity the cases of LPT3233 are encapsulated in water clear plastic T1 3/4 package individualt</p>		
<p>• MAXIMUM RATINGS($T_a=25^\circ\text{C}$)</p>						
PARAMETER		MAXIMUM RATINGS		UNIT		
Power Dissipation		100		mw		
Collector-Emitter Voltage		30		V		
Emitter-Collector Voltage		5		V		
Operating Temperature		-50 $^\circ\text{C}$ TO +100 $^\circ\text{C}$				
Storage Temperature		-50 $^\circ\text{C}$ TO +100 $^\circ\text{C}$				
Lead Soldering Temperature(1.6mm From Body)		260 $^\circ\text{C}$ for 5 seconds				
<p>• ELECTRICAL CHARACTERISTICS($T_a=25^\circ\text{C}$)</p>						
PARAMETER	SYMBOL	Min.	Typ.	Max.	UNIT	TEST CONDITION
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	30			V	$I_c=1\text{mA}$ $E_e=0\text{mw}/\text{cm}^2$
Emitter-Collector Breakdown Voltage	$V_{(BR)ECO}$	5			V	$I_E=100\ \mu\text{A}$ $E_e=0\text{mw}/\text{cm}^2$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$			0.4	V	$I_c=0.5\text{mA}$ $E_e=20\text{mw}/\text{cm}^2$
Rise Time	T_r		5		μs	$V_{CE}=30\text{V}$ $I_C=800\ \mu\text{A}$, $R_L=1\text{K}\Omega$
Fall Time	T_f		5		μs	
Collector Dark Current	I_{CEO}			100	nA	$V_{CE}=10\text{V}$ $E_e=0\text{mw}/\text{cm}^2$
On State Collector Current	$I_p(\text{on})$	1		2	mA	$V_{CE}=5\text{v}$ $E_e=1\text{mw}/\text{cm}^2$ $\lambda P=940\text{nm}$
		2		4	mA	
		4		8	mA	
		8			mA	
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